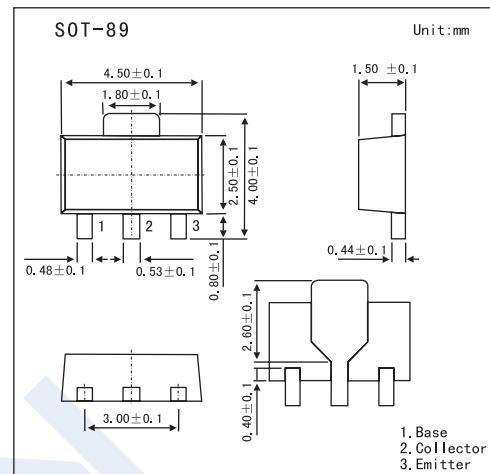


High-Voltage Driver Applications

2SC4548

■ Features

- High Breakdown Voltage
- Adoption of MBIT Process
- Excellent h_{FE} Linearity.



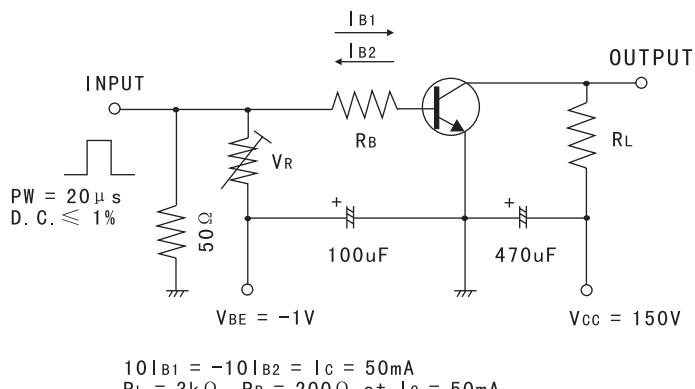
■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C	200	mA
Collector Current (Pulse)	I_{CP}	400	mA
Collector Power Dissipation	P_C^*	1.3	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

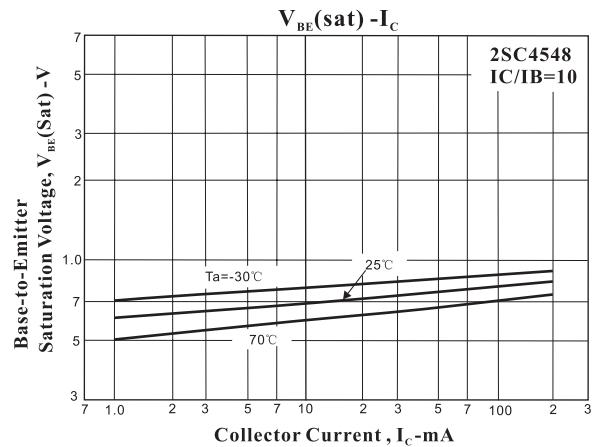
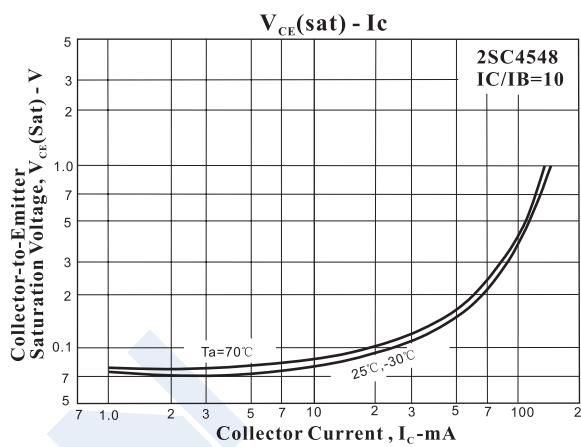
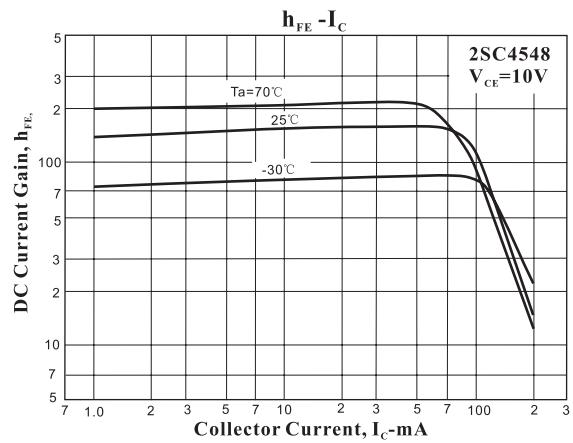
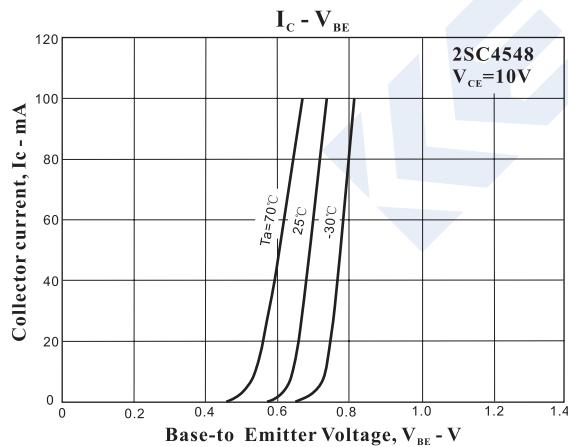
* Mounted on ceramic board (250 mm² x 0.8 mm)

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector Cut-off Current	I_{CBO}	$V_{CB} = 300\text{V}$, $I_E = 0$			0.1	μA
Emitter Cut-off Current	I_{EBO}	$V_{EB} = 4\text{V}$, $I_C = 0$			0.1	μA
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$, $I_E = 0$	400			V
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $R_{BE} = \infty$	400			V
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$, $I_C = 0$	5			V
DC Current Gain	h_{FE}	$V_{CE} = 10\text{V}$, $I_C = 50\text{mA}$	60		200	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 50\text{mA}$, $I_B = 5\text{mA}$			0.8	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	$I_C = 50\text{mA}$, $I_B = 5\text{mA}$			1	V
Gain-Bandwidth Product	f_T	$V_{CE} = 30\text{V}$, $I_C = 10\text{mA}$	70			MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 30\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	5			pF
Reverse Transfer Capacitance	C_{re}	$V_{CB} = 30\text{V}$, $I_E = 0$, $f = 1\text{MHz}$	4			pF
Turn-On Time	t_{on}	See Test Circuit.		0.25		μs
Turn-Off Time	t_{off}			5.0		

2SC4548**■ Test Circuit****■ hFE Classification**

Marking	CN	
Rank	D	E
hFE	$60 \sim 120$	$100 \sim 200$

■ Electrical Characteristics Curves

2SC4548